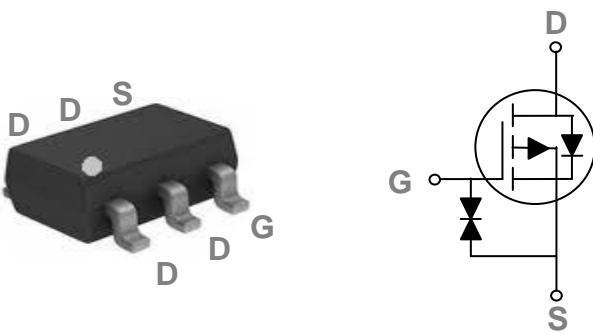


General Description

These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

SOT23-6L Pin Configuration



BVDSS	RDSON	ID
-20V	33mΩ	-5.8A

Features

- -20V, -5.8A, $R_{DS(ON)} = 33m\Omega @ V_{GS} = -4.5V$
- Improved dv/dt capability
- Fast switching
- Green Device Available
- Suit for -1.8V Gate Drive Applications

Applications

- Notebook
- Load Switch
- Networking

Absolute Maximum Ratings $T_c=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 10	V
I_D	Drain Current – Continuous ($T_c=25^\circ C$)	-5.8	A
	Drain Current – Continuous ($T_c=100^\circ C$)	-3.7	A
I_{DM}	Drain Current – Pulsed ¹	-23.2	A
P_D	Power Dissipation ($T_c=25^\circ C$)	1.56	W
	Power Dissipation – Derate above $25^\circ C$	0.012	W/ $^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	80	$^\circ C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-20	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.02	---	V/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-20V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-16V, V _{GS} =0V, T _J =125°C	---	---	-10	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±10V, V _{DS} =0V	---	---	±10	uA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-4.5V, I _D =-4A	---	28	33	mΩ
		V _{GS} =-2.5V, I _D =-3A	---	37	45	
		V _{GS} =-1.8V, I _D =-2A	---	49	65	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-0.3	-0.6	-1	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	2	---	mV/°C
gfs	Forward Transconductance	V _{DS} =-10V, I _S =-3A	---	8.4	---	S

Dynamic and switching Characteristics

Q _g	Total Gate Charge ^{2,3}	V _{DS} =-10V, V _{GS} =-4.5V, I _D =-4A	---	16.1	25	nC
Q _{gs}	Gate-Source Charge ^{2,3}		---	1.8	3	
Q _{gd}	Gate-Drain Charge ^{2,3}		---	3.8	7	
T _{d(on)}	Turn-On Delay Time ^{2,3}	V _{DD} =-10V, V _{GS} =-4.5V, R _G =25Ω I _D =-1A	---	8.2	16	nS
T _r	Rise Time ^{2,3}		---	30	57	
T _{d(off)}	Turn-Off Delay Time ^{2,3}		---	71.1	135	
T _f	Fall Time ^{2,3}		---	19.8	38	
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, F=1MHz	---	1440	2100	pF
C _{oss}	Output Capacitance		---	155	230	
C _{rss}	Reverse Transfer Capacitance		---	115	170	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	-5.8	A
I _{SM}	Pulsed Source Current		---	---	-23.2	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
3. Essentially independent of operating temperature.

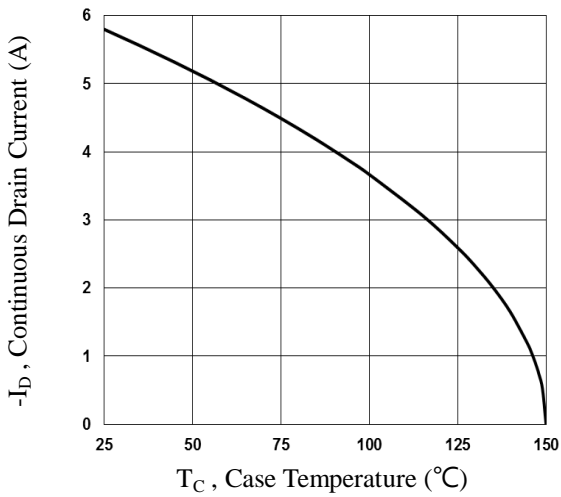


Fig.1 Continuous Drain Current vs. T_c

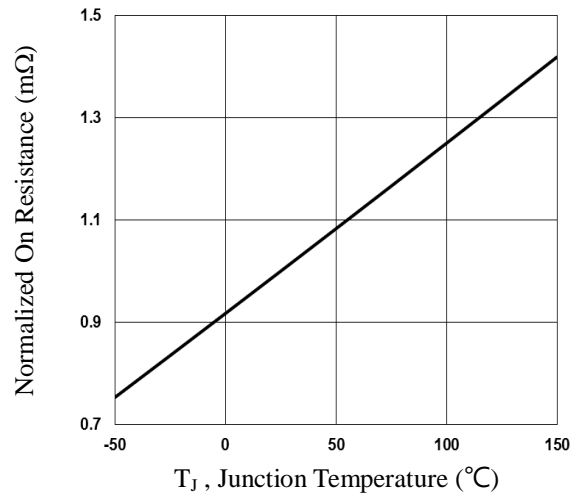


Fig.2 Normalized $R_{DS(on)}$ vs. T_j

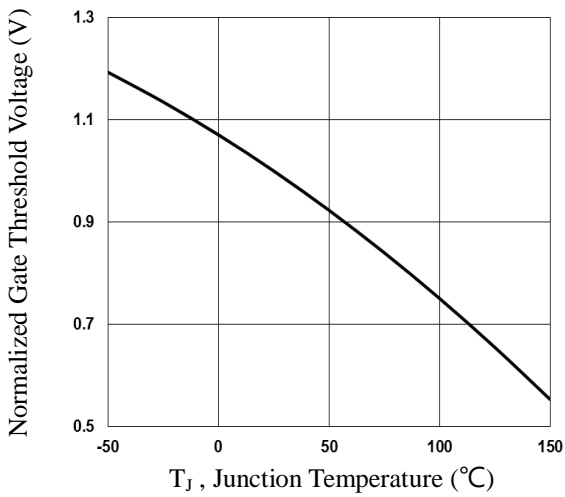


Fig.3 Normalized V_{th} vs. T_j

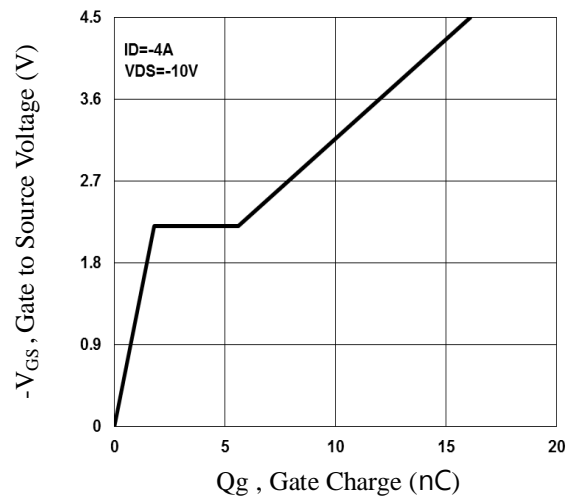


Fig.4 Gate Charge Waveform

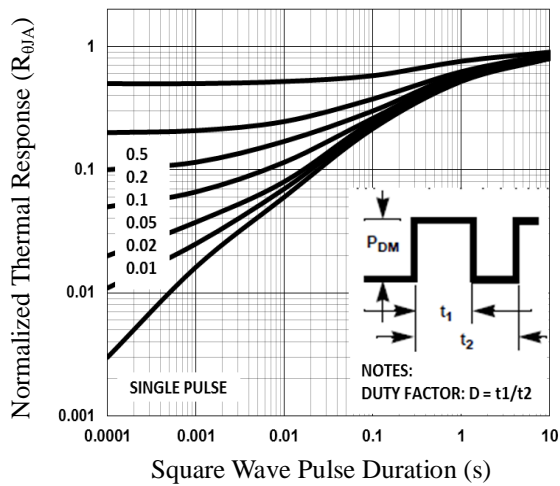


Fig.5 Normalized Transient Impedance

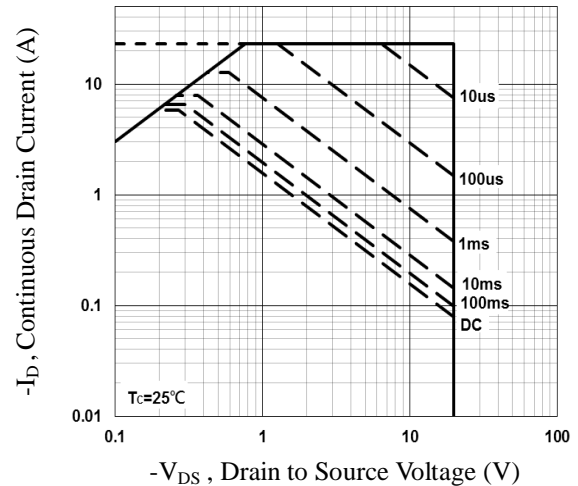


Fig.6 Maximum Safe Operation Area

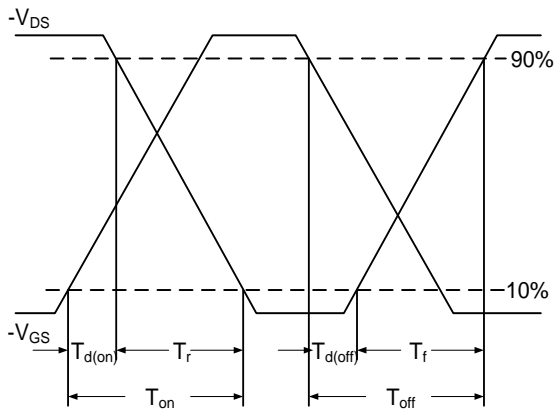


Fig.7 Switching Time Waveform

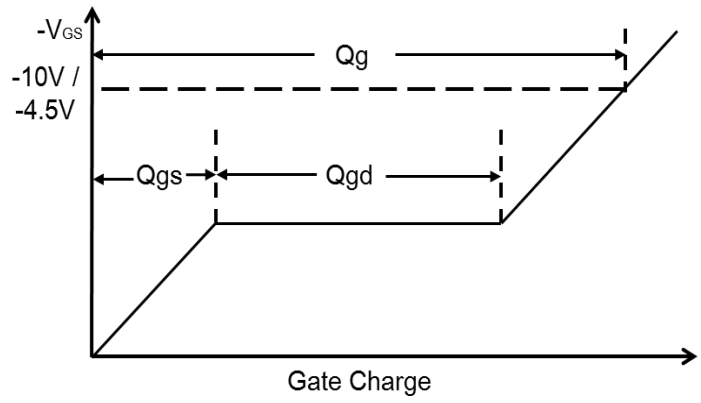
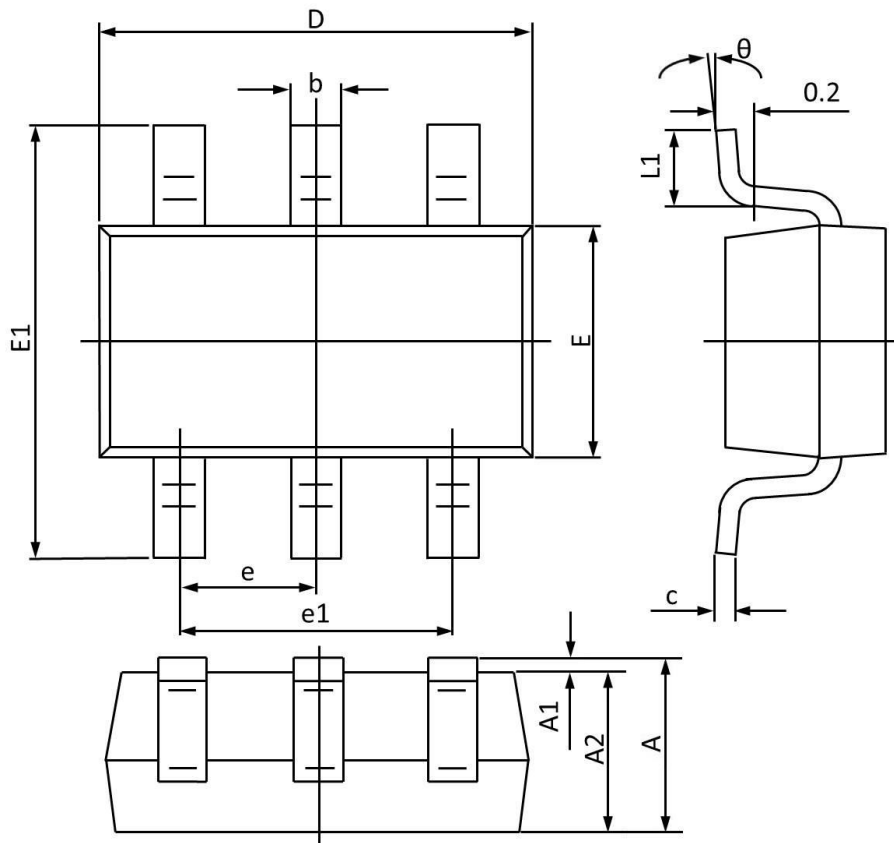


Fig.8 Gate Charge Waveform

SOT23-6L PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.450	-	0.057	-
A1	0.100	0.000	0.004	0.000
A2	1.300	1.050	0.051	0.041
b	0.500	0.300	0.020	0.012
c	0.200	0.100	0.008	0.004
D	3.100	2.700	0.122	0.106
E	1.800	1.400	0.071	0.055
E1	3.000	2.600	0.118	0.102
e	0.95BSC		0.037BSC	
e1	2.000	1.800	0.079	0.071
L1	0.600	0.300	0.024	0.012
θ	10°	0°	10°	0°